

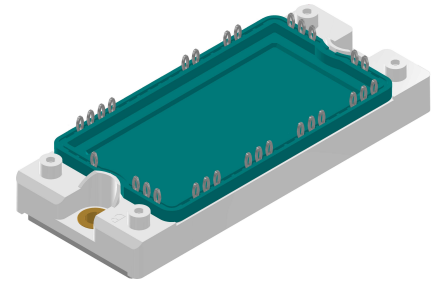
# High Voltage Standard Rectifier Module

3~ Rectifier	Brake Chopper
$V_{RRM} = 2200\text{ V}$	$V_{CES} = 1700\text{ V}$
$I_{DAV} = 210\text{ A}$	$I_{C25} = 145\text{ A}$
$I_{FSM} = 1000\text{ A}$	$V_{CE(sat)} = 1.8\text{ V}$

3~ Rectifier Bridge + Brake Unit + NTC

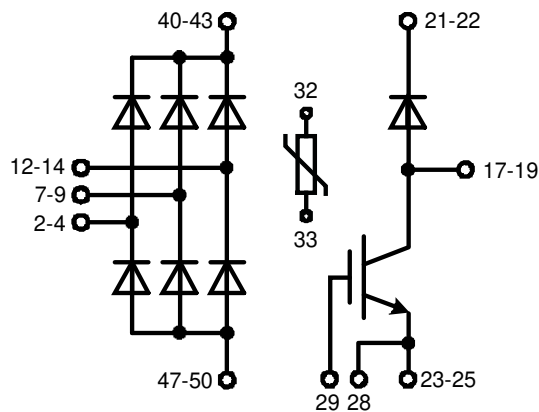
Part number

**MDNA210UB2200PTED**



Backside: isolated

 E72873



### Features / Advantages:

- Brake with Infineon IGBT<sup>3</sup>

### Applications:

- 3~ Rectifier with brake unit for drive inverters

### Package: E2-Pack

- Isolation Voltage: 3600 V~
- Industry standard outline
- RoHS compliant
- PressFit-Pins for PCB mounting
- Height: 17 mm
- Base plate: Copper internally DCB isolated
- Advanced power cycling
- Phase Change Material available

### Disclaimer Notice

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Rectifier				Ratings			
Symbol	Definition	Conditions		min.	typ.	max.	Unit
$V_{RSM}$	max. non-repetitive reverse blocking voltage					2300	V
$V_{RRM}$	max. repetitive reverse blocking voltage					2200	V
$I_R$	reverse current	$V_R = 2200$ V		$T_{VJ} = 25^\circ\text{C}$		100	$\mu\text{A}$
		$V_R = 2200$ V		$T_{VJ} = 150^\circ\text{C}$		2	mA
$V_F$	forward voltage drop	$I_F = 70$ A		$T_{VJ} = 25^\circ\text{C}$		1.23	V
		$I_F = 210$ A				1.75	V
		$I_F = 70$ A		$T_{VJ} = 125^\circ\text{C}$		1.19	V
		$I_F = 210$ A				1.67	V
$I_{DAV}$	bridge output current	$T_C = 85^\circ\text{C}$	rectangular	$T_{VJ} = 150^\circ\text{C}$		210	A
$V_{FO}$	threshold voltage	} for power loss calculation only		$T_{VJ} = 150^\circ\text{C}$		0.82	V
$r_F$	slope resistance					5.2	m $\Omega$
$R_{thJC}$	thermal resistance junction to case					0.5	K/W
$R_{thCH}$	thermal resistance case to heatsink				0.1		K/W
$P_{tot}$	total power dissipation			$T_C = 25^\circ\text{C}$		250	W
$I_{FSM}$	max. forward surge current	$t = 10$ ms; (50 Hz), sine		$T_{VJ} = 45^\circ\text{C}$		1.00	kA
		$t = 8,3$ ms; (60 Hz), sine		$V_R = 0$ V		1.08	kA
		$t = 10$ ms; (50 Hz), sine		$T_{VJ} = 150^\circ\text{C}$		850	A
		$t = 8,3$ ms; (60 Hz), sine		$V_R = 0$ V		920	A
$I^2t$	value for fusing	$t = 10$ ms; (50 Hz), sine		$T_{VJ} = 45^\circ\text{C}$		5.00	kA <sup>2</sup> s
		$t = 8,3$ ms; (60 Hz), sine		$V_R = 0$ V		4.85	kA <sup>2</sup> s
		$t = 10$ ms; (50 Hz), sine		$T_{VJ} = 150^\circ\text{C}$		3.62	kA <sup>2</sup> s
		$t = 8,3$ ms; (60 Hz), sine		$V_R = 0$ V		3.52	kA <sup>2</sup> s
$C_J$	junction capacitance	$V_R = 400$ V; $f = 1$ MHz		$T_{VJ} = 25^\circ\text{C}$		33	pF



Brake IGBT + Diode				Ratings			
Symbol	Definition	Conditions	min.	typ.	max.	Unit	
$V_{CES}$	collector emitter voltage	$T_{VJ} = 25^{\circ}C$			1700	V	
$V_{GES}$	max. DC gate voltage				$\pm 20$	V	
$V_{GEM}$	max. transient gate emitter voltage				$\pm 30$	V	
$I_{C25}$	collector current	$T_C = 25^{\circ}C$			145	A	
$I_{C80}$		$T_C = 80^{\circ}C$			100	A	
$P_{tot}$	total power dissipation	$T_C = 25^{\circ}C$			540	W	
$V_{CE(sat)}$	collector emitter saturation voltage	$I_C = 75\text{ A}; V_{GE} = 15\text{ V}$		1.8	2.16	V	
				2.1		V	
$V_{GE(th)}$	gate emitter threshold voltage	$I_C = 4\text{ mA}; V_{GE} = V_{CE}$	5.2	5.8	6.4	V	
$I_{CES}$	collector emitter leakage current	$V_{CE} = V_{CES}; V_{GE} = 0\text{ V}$			0.1	mA	
				0.7		mA	
$I_{GES}$	gate emitter leakage current	$V_{GE} = \pm 20\text{ V}$			500	nA	
$Q_{G(on)}$	total gate charge	$V_{CE} = 900\text{ V}; V_{GE} = 15\text{ V}; I_C = 75\text{ A}$		1200		nC	
$t_{d(on)}$	turn-on delay time	inductive load $V_{CE} = 900\text{ V}; I_C = 75\text{ A}$ $V_{GE} = \pm 15\text{ V}; R_G = 3.9\ \Omega$	$T_{VJ} = 125^{\circ}C$		320	ns	
$t_r$	current rise time				50	ns	
$t_{d(off)}$	turn-off delay time				550	ns	
$t_f$	current fall time				400	ns	
$E_{on}$	turn-on energy per pulse				15	mJ	
$E_{off}$	turn-off energy per pulse				18	mJ	
<b>RBSOA</b>	reverse bias safe operating area	$V_{GE} = \pm 15\text{ V}; R_G = 3.9\ \Omega$					
$I_{CM}$		$V_{CEK} = 1700\text{ V}$			200	A	
<b>SCSOA</b>	short circuit safe operating area	$V_{CEK} = 1700\text{ V}$					
$t_{SC}$	short circuit duration	$V_{CE} = 900\text{ V}; V_{GE} = \pm 15$			10	$\mu s$	
$I_{SC}$	short circuit current	$R_G = 3.9\ \Omega$ ; non-repetitive		400		A	
$R_{thJC}$	thermal resistance junction to case				0.23	K/W	
$R_{thCH}$	thermal resistance case to heatsink			0.08		K/W	
<b>Brake Diode</b>							
$V_{RRM}$	max. repetitive reverse voltage				1700	V	
$I_{F25}$	forward current				81	A	
$I_{F80}$					54	A	
$V_F$	forward voltage	$I_F = 60\text{ A}$			2.20	V	
				2.00		V	
$I_R$	reverse current	$V_R = V_{RRM}$			0.1	mA	
					1.2	mA	
$Q_{rr}$	reverse recovery charge	$V_R = 900\text{ V}$ $-di_f/dt = 1600\text{ A}/\mu s$ $I_F = 60\text{ A}; V_{GE} = 0\text{ V}$	$T_{VJ} = 125^{\circ}C$		15	$\mu C$	
$I_{RM}$	max. reverse recovery current				100	A	
$t_{rr}$	reverse recovery time				550	ns	
$E_{rec}$	reverse recovery energy				6.5	mJ	
$R_{thJC}$	thermal resistance junction to case				0.6	K/W	
$R_{thCH}$	thermal resistance case to heatsink			0.2		K/W	

Package E2-Pack		Ratings				
Symbol	Definition	Conditions	min.	typ.	max.	Unit
$I_{RMS}$	RMS current	per terminal			30	A
$T_{VJ}$	virtual junction temperature		-40		150	°C
$T_{op}$	operation temperature		-40		125	°C
$T_{stg}$	storage temperature		-40		125	°C
<b>Weight</b>				176		g
$M_D$	mounting torque		3		6	Nm
$d_{Spp/App}$	creepage distance on surface / striking distance through air	terminal to terminal	6.0			mm
$d_{Spb/Apb}$		terminal to backside	12.0			mm
$V_{ISOL}$	isolation voltage	t = 1 second t = 1 minute	3600			V
		50/60 Hz, RMS; $I_{ISOL} \leq 1$ mA	3000			V


**Part description**

M = Module  
 D = Diode  
 N = High Voltage Standard Rectifier  
 A = (>= 2000V)  
 210 = Current Rating [A]  
 UB = 3- Rectifier Bridge + Brake Unit  
 2200 = Reverse Voltage [V]  
 PT = PressFit-Pin, Thermistor  
 ED = E2-Pack  
 - = Hyphen  
 PC = Phase Change Material

Ordering	Ordering Number	Marking on Product	Delivery Mode	Quantity	Code No.
Standard	MDNA210UB2200PTED	MDNA210UB2200PTED	Blister	28	515668
Alternative	MDNA210UB2200PTED-PC	MDNA210UB2200PTED	Blister	28	515430

**Temperature Sensor NTC**

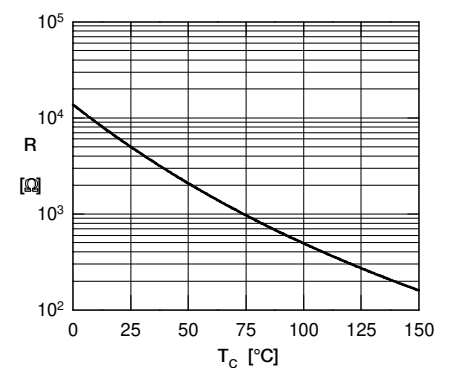
Symbol	Definition	Conditions	min.	typ.	max.	Unit
$R_{25}$	resistance	$T_{VJ} = 25^\circ$	4.85	5	5.15	k $\Omega$
$B_{25/50}$	temperature coefficient			3375		K

**Equivalent Circuits for Simulation**

\* on die level

 $T_{VJ} = 150^\circ\text{C}$ 

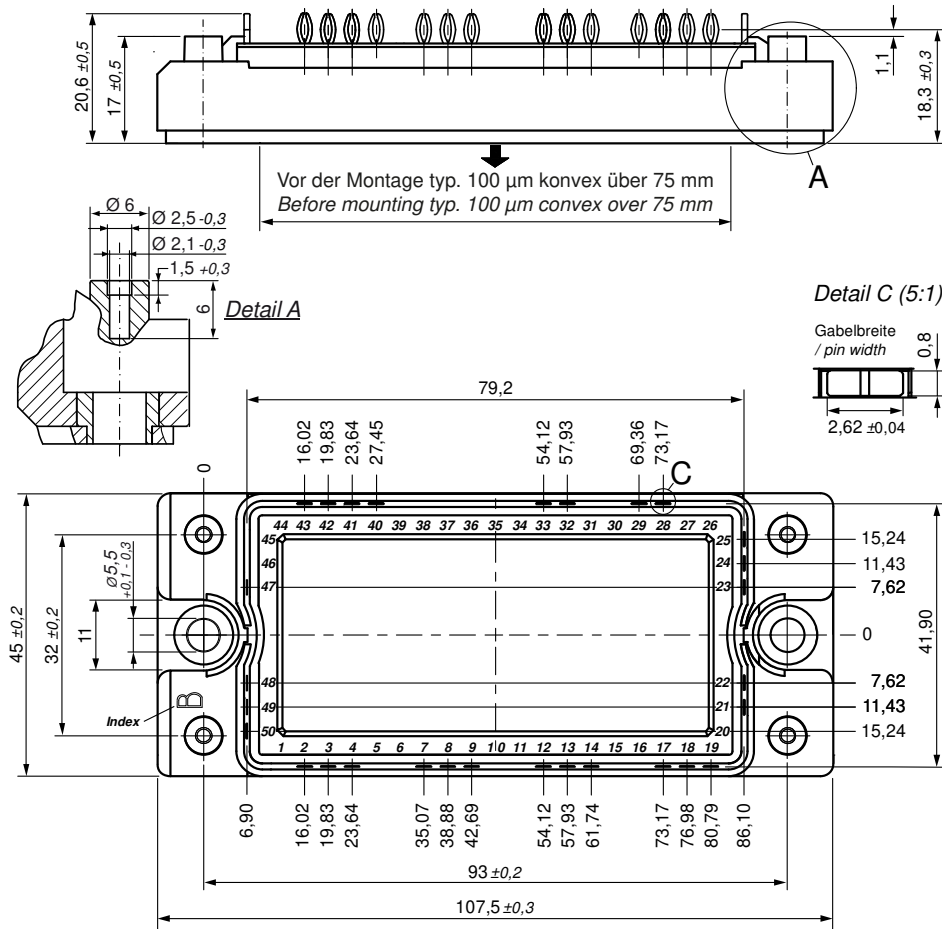
		Rectifier	Brake IGBT +	Brake Diode	
$V_0$	threshold voltage	0.82	1.1	1.22	V
$R_0$	slope resistance *	3.1	17.9	13	m $\Omega$



Typ. NTC resistance vs. temperature



**Outlines E2-Pack**

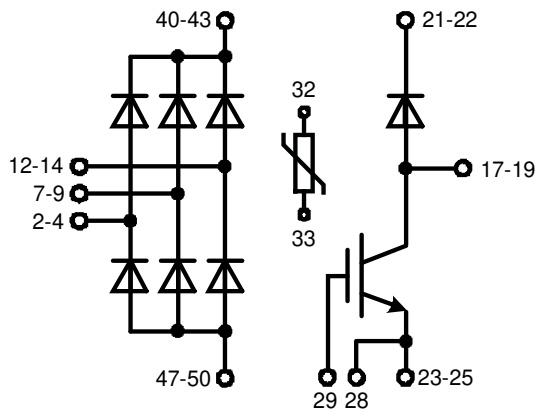


**Bemerkung / Note:**

- Nicht tolerierte Maße nach / Measure without tolerances according DIN ISO 2768-T1-m
- PCB-Lochmuster / PCB hole pattern: **see pin position**
- Toleranz Pin-Position und PCB-Lochmuster / Tolerance of pin position and PCB hole pattern:  $\oplus 0.1$
- Bohrlochdurchmesser / Diameter of drill:  $\varnothing 2.35$  mm
- Endlochdurchmesser / Diameter of plated holes:  $\varnothing 2.14 - 2.29$  mm (Cu thickness in via typ.  $50 \mu\text{m}$ )
- Beschichtung / Plating: **chem. Sn max.  $15 \mu\text{m}$**
- Einpresskraft / Insert Force: per terminal with a typ. insert speed of  $7$  mm/s: **typ. 90 N**
- Weitere Angaben / Further information: [www.ixys.com](http://www.ixys.com) **Application note IXAN0077**
- Montageanleitung / Mounting instruction: [www.ixys.com](http://www.ixys.com) **Application note IXAN0024**

**Detail A:** PCB-Montage / Mounting on PCB<sup>L</sup>

- Empfohlene, selbstschneidende Schraube / Recommended, self-tapping screw: **EJOT PT®** (Größe / size: **K25**)<sup>L</sup>
- Max. Schraubenlänge / Max. screw length: **PCB-Dicke / thickness + 6 mm** (max. Lochtiefe / hole depth)<sup>L</sup>
- Empfohlenes Drehmoment / Recommended mounting torque: **1.5 Nm**



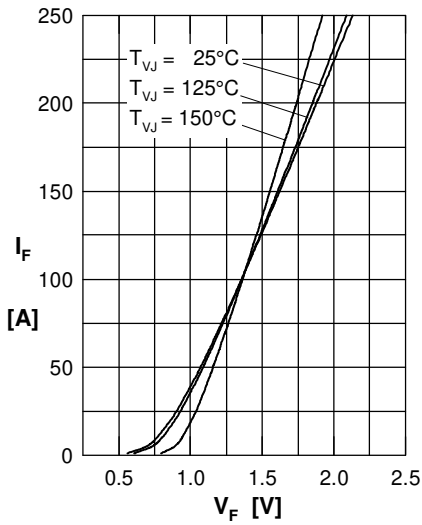
**Rectifier**


Fig. 1 Forward current versus voltage drop per diode

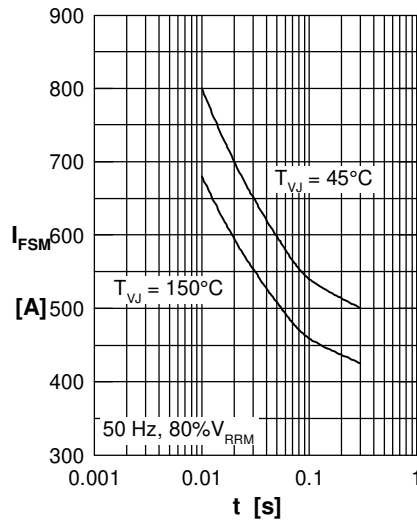


Fig. 2 Surge overload current vs. time per diode

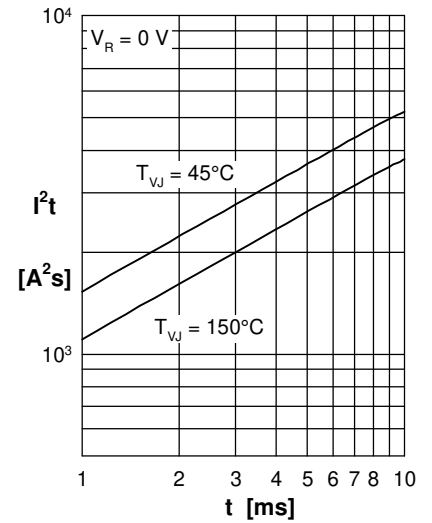
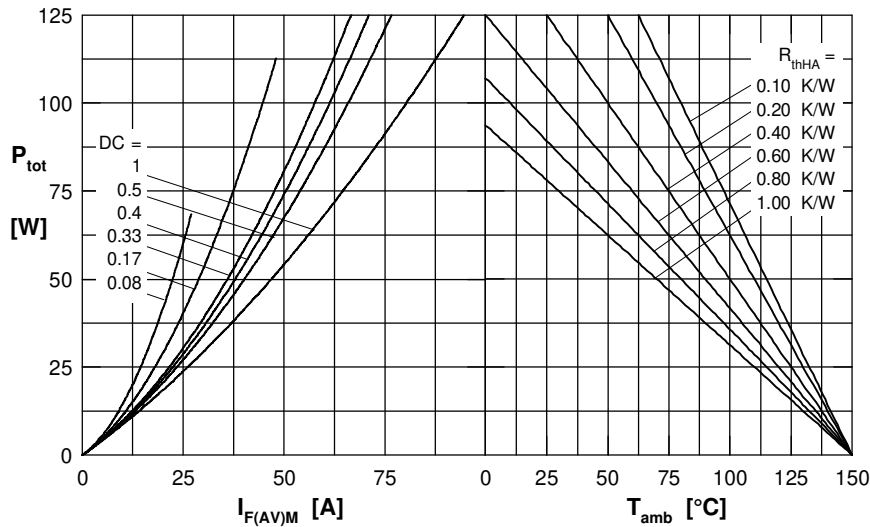

 Fig. 3  $I^2t$  versus time per diode


Fig. 4 Power dissipation vs. forward current and ambient temperature per diode

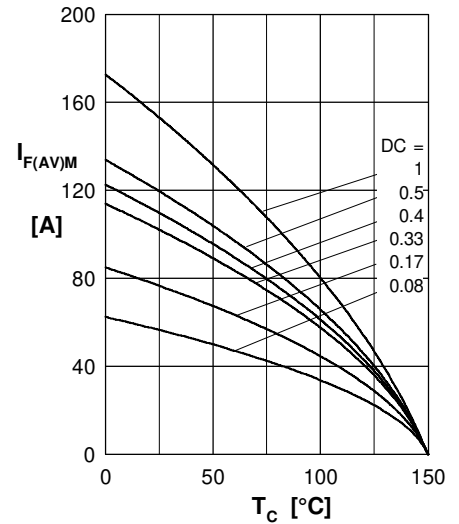


Fig. 5 Max. forward current vs. case temperature per diode

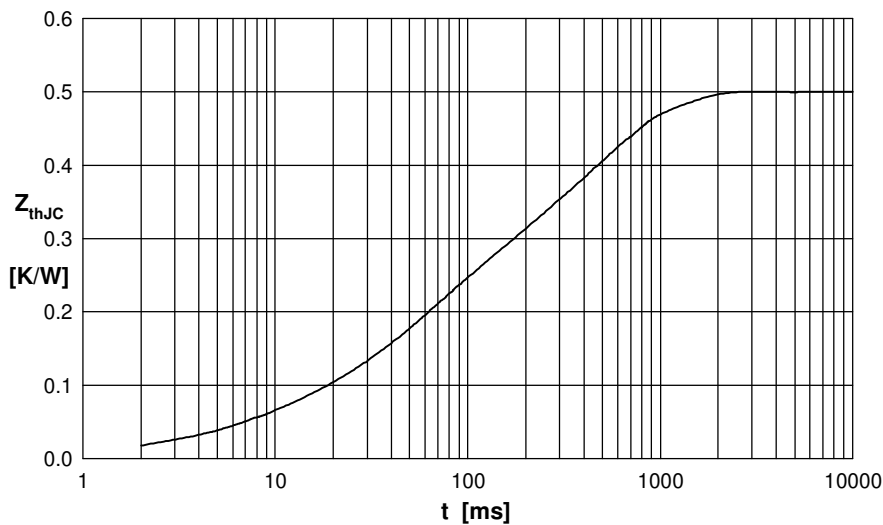


Fig. 6 Transient thermal impedance junction to case vs. time per diode

 Constants for  $Z_{thJC}$  calculation:

i	$R_{thi}$ (K/W)	$t_i$ (s)
1	0.030	0.006
2	0.003	0.007
3	0.182	0.045
4	0.285	0.450

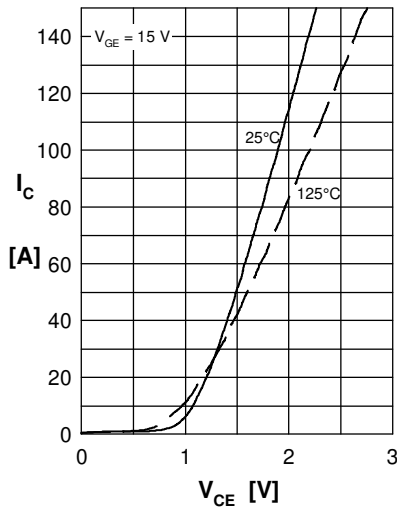
**Brake IGBT + Diode**


Fig.1 Output characteristics IGBT

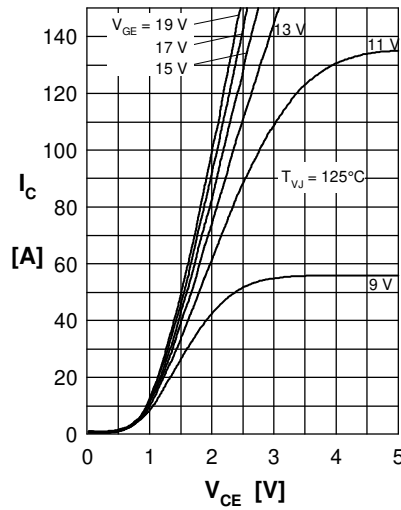


Fig.2 Typ. output characteristics IGBT

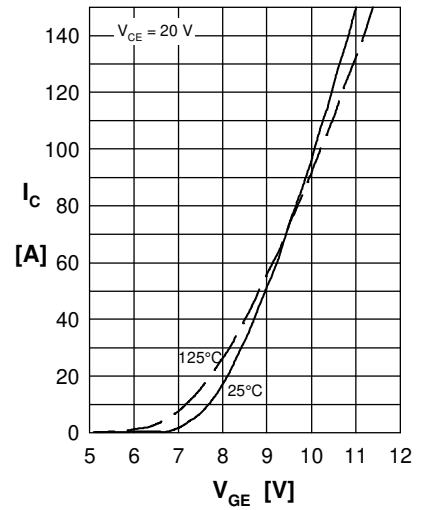


Fig.3 Typ. transfer charact. IGBT

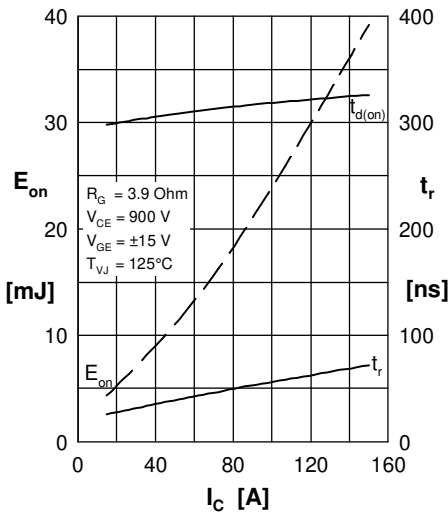


Fig.4 Typ. turn-on energy &amp; switch. times vs. collector current

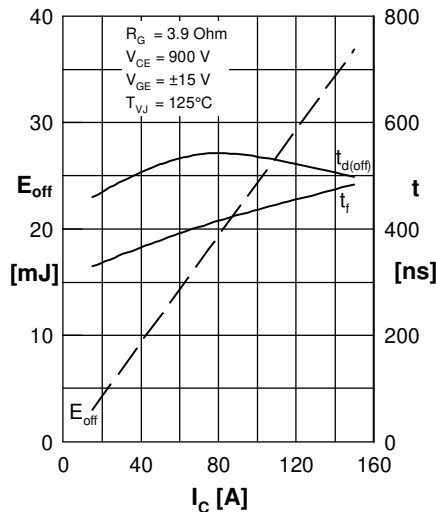


Fig.5 Typ. turn-off energy &amp; switch. times vs. collector current

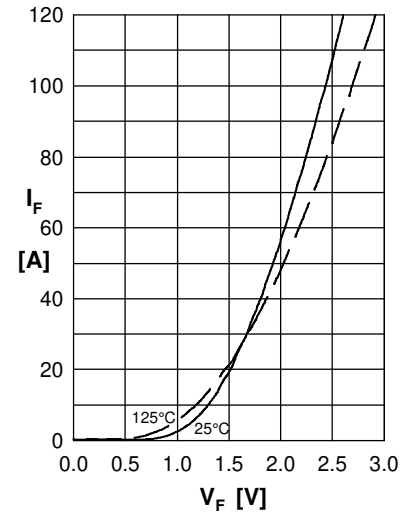


Fig.6 Typ. forward characteristics Diode

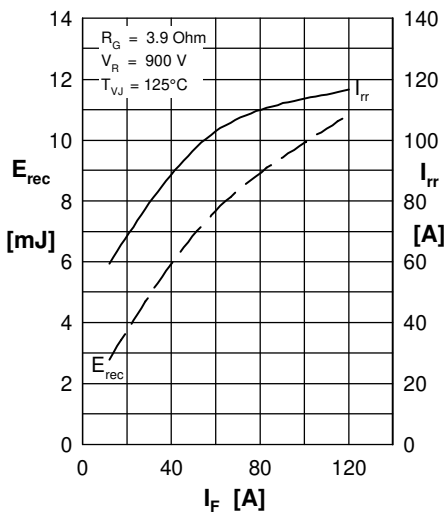


Fig.7 Typ. reverse recovery characteristics Diode

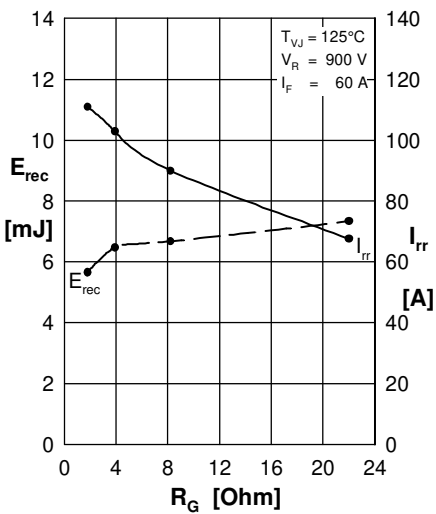


Fig.8 Typ. reverse recovery characteristics Diode

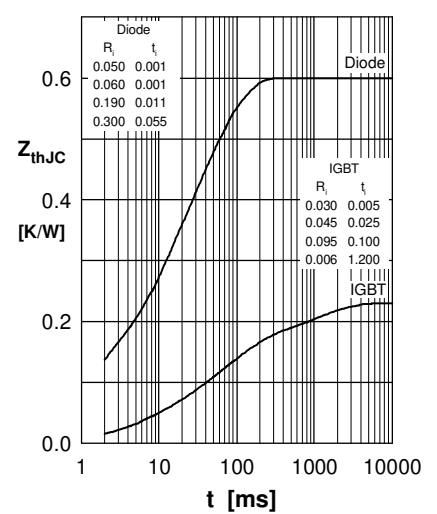


Fig.9 Transient thermal resistance junction to case